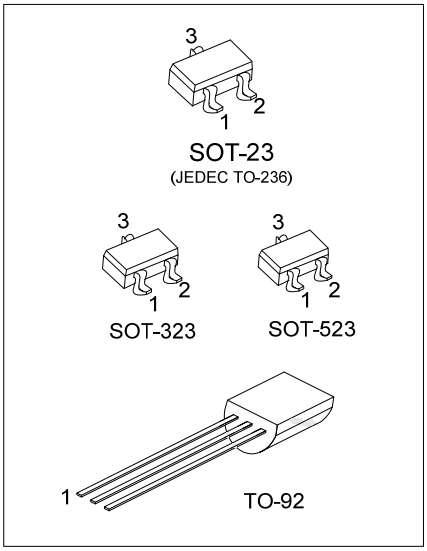
DTC123E

NPN SILICON TRANSISTOR

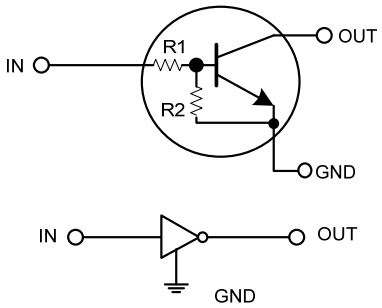
DIGITAL TRANSISTORS (BUILT- IN RESISTORS)



■ FEATURES

* Built-in bias resistors that implies easy ON/OFF applications.
* The bias resistors are thin-film resistors with complete isolation to allow negative input.

■ EQUIVALENT CIRCUIT



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
DTC123EL-AE3-R	DTC123EG-AE3-R	SOT-23	I	G	O	Tape Reel
DTC123EL-AL3-R	DTC123EG-AL3-R	SOT-323	I	G	O	Tape Reel
DTC123EL-AN3-R	DTC123EG-AN3-R	SOT-523	I	G	O	Tape Reel
DTC123EL-T92-B	DTC123EG-T92-B	TO-92	G	O	I	Tape Box
DTC123EL-T92-K	DTC123EG-T92-K	TO-92	G	O	I	Bluk

Note: Pin Assignment: I: IN G: GND O: OUT

DTC123EG-AE3-R
(1)Packing Type
(2)Package Type
(3)Green Package

(1) B: Tape Box, K: Bluk, R: Tape Reel
(2) AE3: SOT-23, AL3: SOT-323, AN3: SOT-523
T92: TO-92
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

SOT-23 / SOT-323 / SOT-523	TO-92
CC3E E: Lead Free E: Halogen Free	UTC DTC123E□ □□□ 1 L: Lead Free G: Halogen Free Date Code

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless others specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Supply Voltage		V_{CC}	50	V
Input Voltage		V_{IN}	-10 ~ +12	V
Output Current		I_{OUT}	100	mA
Power Dissipation	SOT-523	P_D	150	mW
	SOT-23/SOT-323		200	mW
	TO-92		625	mW
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

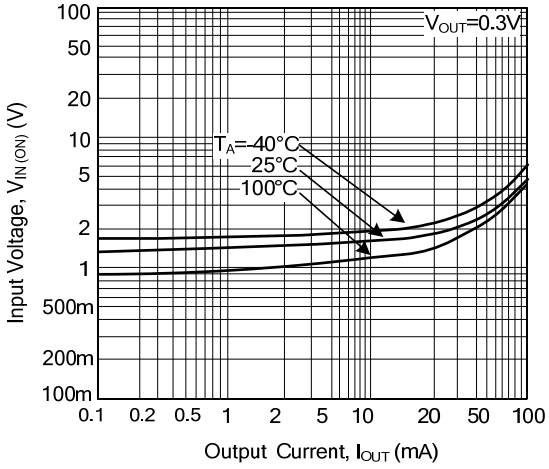
■ ELECTRICAL SPECIFICATIONS (T_A=25°C, unless others specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input Voltage	$V_{IN(OFF)}$	V_{CC} =5V, I_{OUT} =100μA			0.5	V
	$V_{IN(ON)}$	V_{OUT} =0.3V, I_{OUT} =20mA	3			
Output Voltage	$V_{OUT(ON)}$	I_{OUT}/I_{IN} =10mA/0.5mA		0.1	0.3	V
Input Current	I_{IN}	V_{IN}=5V			3.8	mA
Output Current	$I_{OUT(OFF)}$	V_{CC} =50V, V_{IN} =0V			0.5	μA
DC Current Gain	h_{FE}	V_{OUT} =5V, I_{OUT} =20mA	20			
Input Resistance	R_1		1.54	2.2	2.86	KΩ
Resistance Ratio	R_2/R_1		0.8	1	1.2	
Transition Frequency	f_T	V_{CE} =10V, I_E =−5mA, f=100MHz (Note)		250		MHz

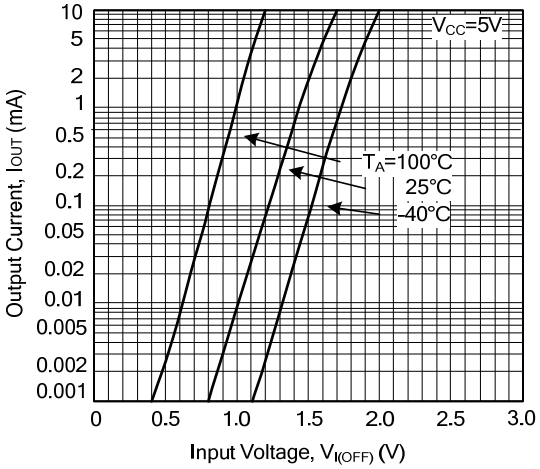
Note: Transition frequency of the device

■ TYPICAL CHARACTERISTIC

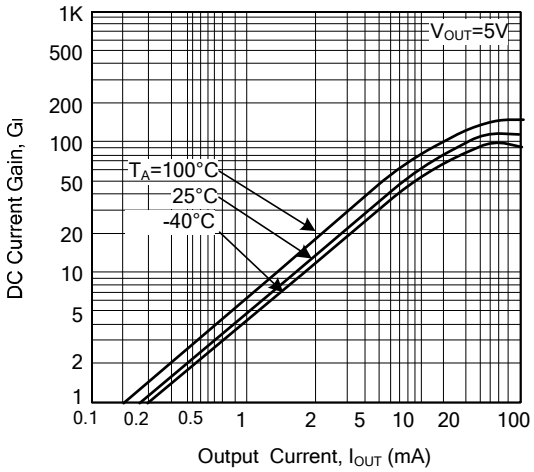
Input Voltage vs. Output Current
(ON Characteristics)



Output Current vs. Input Voltage
(OFF Characteristics)



DC Current Gain vs. Output Current



Output Voltage vs. Output Current